

TOSHIBA**TC74LCX257F/FN/FT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74LCX257F, TC74LCX257FN, TC74LCX257FT**LOW VOLTAGE QUAD 2-CHANNEL MULTIPLEXER (3-STATE)
WITH 5V TOLERANT INPUTS AND OUTPUTS**

The TC74LCX257 is a high performance CMOS MULTIPLEXER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

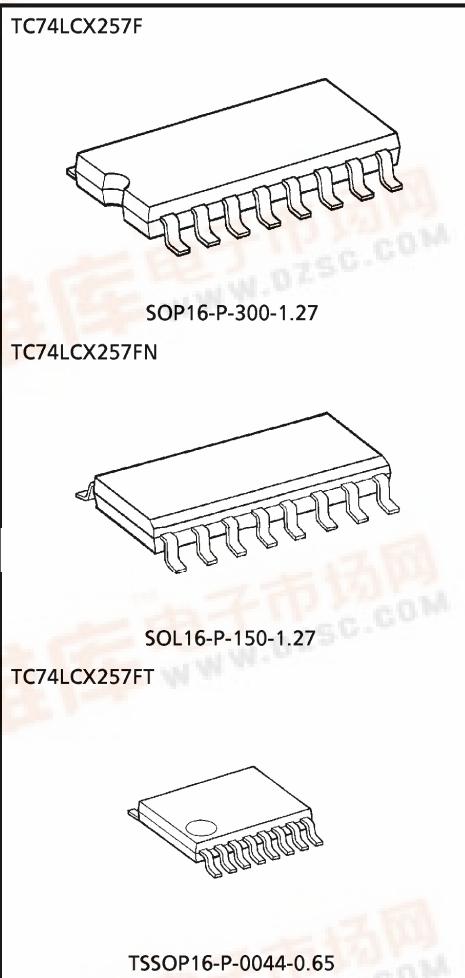
The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for inputs.

It is composed of four independent 2-channel multiplexers with common SELECT and OUTPUTENABLE (OE).

If OE is set low, the outputs are held in a high-impedance state. When SELECT is set low, "A" data inputs are enabled. Conversely, when SELECT is high, "B" data inputs are enabled.

All inputs are equipped with protection circuits against static discharge.

(Note) The JEDEC SOP (FN) is not available in Japan.

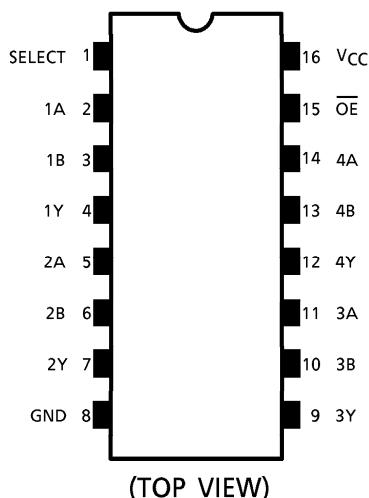


Weight
 SOP16-P-300-1.27 : 0.18g (Typ.)
 SOL16-P-150-1.27 : 0.12g (Typ.)
 TSSOP16-P-0044-0.65 : 0.06g (Typ.)

961001EBA2

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PIN ASSIGNMENT



(TOP VIEW)

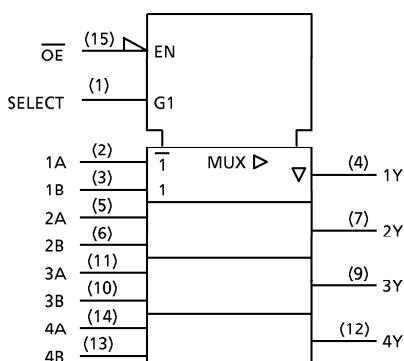
TRUTH TABLE

INPUTS			OUTPUTS	
\overline{OE}	SELECT	A	B	Y
H	X	X	X	Z
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

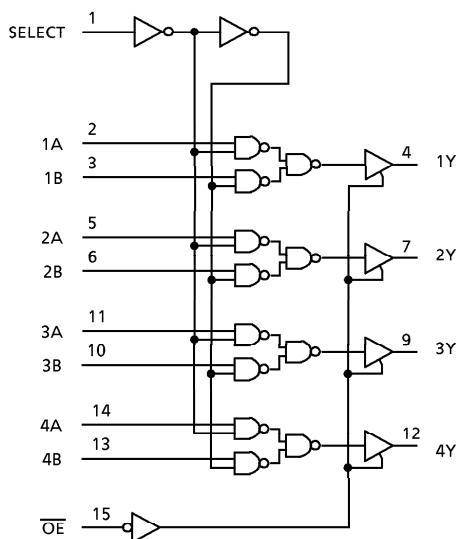
X : Don't Care

Z : High-impedance

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



- 961001EBA2'
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 - The information contained herein is subject to change without notice.

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~7.0	V
DC Output Voltage	V_{OUT}	-0.5~7.0 (Note 1)	V
		-0.5~ V_{CC} +0.5 (Note 2)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	± 50 (Note 3)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	180	mW
DC V_{CC} /Ground Current	I_{CC}/I_{GND}	± 100	mA
Storage Temperature	T_{stg}	-65~150	°C

(Note 1) Output in Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) $V_{OUT} < GND, V_{OUT} > V_{CC}$

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	± 24 (Note 7)	mA
		± 12 (Note 8)	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns/V

(Note 4) Data Retention Only

(Note 5) Output in Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6V$ (Note 8) $V_{CC} = 2.7 \sim 3.0V$ (Note 9) $V_{IN} = 0.8 \sim 2.0V, V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICSDC CHARACTERISTICS ($T_a = -40\text{~}85^\circ\text{C}$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V_{IH}				2.7~3.6	2.0	—	
Output Voltage	"L" Level	V_{IL}				2.7~3.6	—	0.8	
	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100\mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -12\text{mA}$	2.7	2.2	—		
				$I_{OH} = -18\text{mA}$	3.0	2.4	—		
				$I_{OH} = -24\text{mA}$	3.0	2.2	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100\mu\text{A}$	2.7~3.6	—	0.2	V	
				$I_{OL} = 12\text{mA}$	2.7	—	0.4		
				$I_{OL} = 16\text{mA}$	3.0	—	0.4		
				$I_{OL} = 24\text{mA}$	3.0	—	0.55		
Input Leakage Current	I_{IN}	$V_{IN} = 0\text{~}5.5\text{V}$		2.7~3.6		—	± 5.0	μA	
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\text{~}5.5\text{V}$		2.7~3.6		—	± 5.0	μA	
Power Off Leakage Current	I_{OFF}	$V_{IN} / V_{OUT} = 5.5\text{V}$		0		—	10.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND $V_{IN} / V_{OUT} = 3.6\text{~}5.5\text{V}$		2.7~3.6		—	10.0	μA	
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6\text{V}$		2.7~3.6		—	500		

AC CHARACTERISTICS ($T_a = -40\text{~}85^\circ\text{C}$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Propagation Delay Time (A, B-Y)	t_{pLH}	(Fig.1, 2)				2.7	—	6.5	
	t_{pHL}					3.3 ± 0.3	1.5	6.0	
Propagation Delay Time (SELECT-Y)	t_{pLH}	(Fig.1, 2)				2.7	—	8.5	
	t_{pHL}					3.3 ± 0.3	1.5	7.0	
Output Enable Time	t_{pZL}	(Fig.1, 3)				2.7	—	8.5	
	t_{pZH}					3.3 ± 0.3	1.5	7.0	
Output Disable Time	t_{pLZ}	(Fig.1, 3)				2.7	—	6.0	
	t_{pHZ}					3.3 ± 0.3	1.5	5.5	
Output To Output Skew	t_{osLH}	(Note 10)				2.7	—	—	
	t_{osHL}					3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design.
 $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

DYNAMIC SWITCHING CHARACTERISTICS (Ta = 25°C, Input $t_r = t_f = 2.5\text{ns}$, $C_L = 50\text{pF}$, $R_L = 500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP.	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$V_{IH} = 3.3\text{V}$, $V_{IL} = 0\text{V}$	3.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	$ V_{OLV} $	$V_{IH} = 3.3\text{V}$, $V_{IL} = 0\text{V}$	3.3	0.8	V

CAPACITIVE CHARACTERISTICS (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP.	UNIT	
Input Capacitance	C_{IN}	—	3.3	7	pF	
Output Capacitance	C_{OUT}	—	3.3	8	pF	
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10\text{MHz}$	(Note 11)	3.3	25	pF

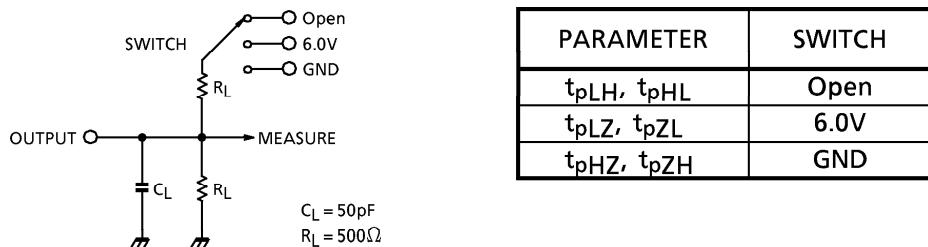
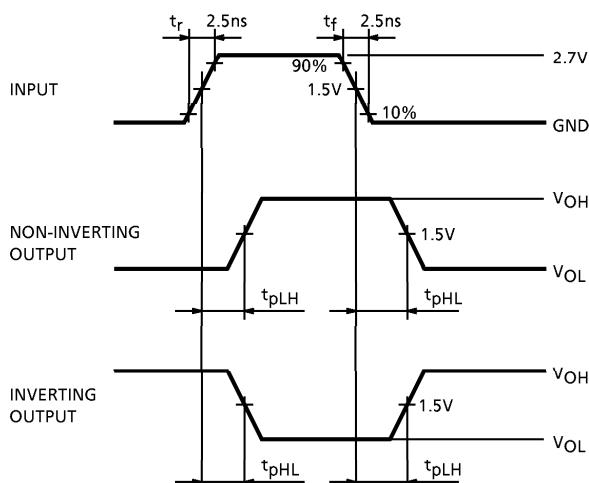
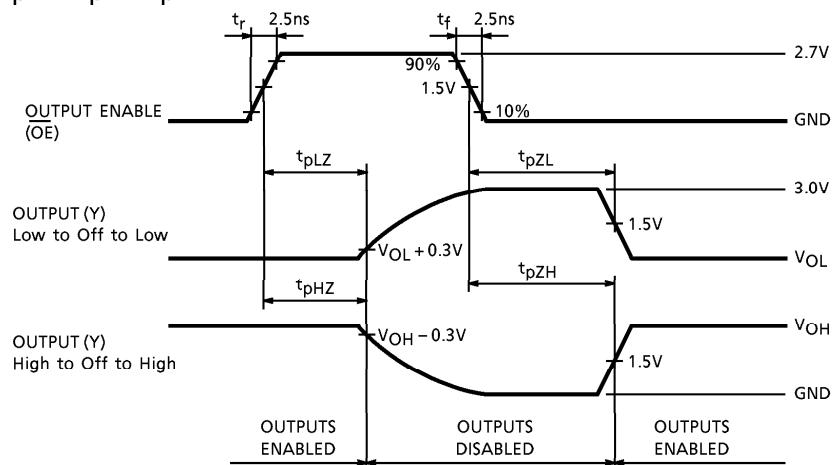
(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

TEST CIRCUIT

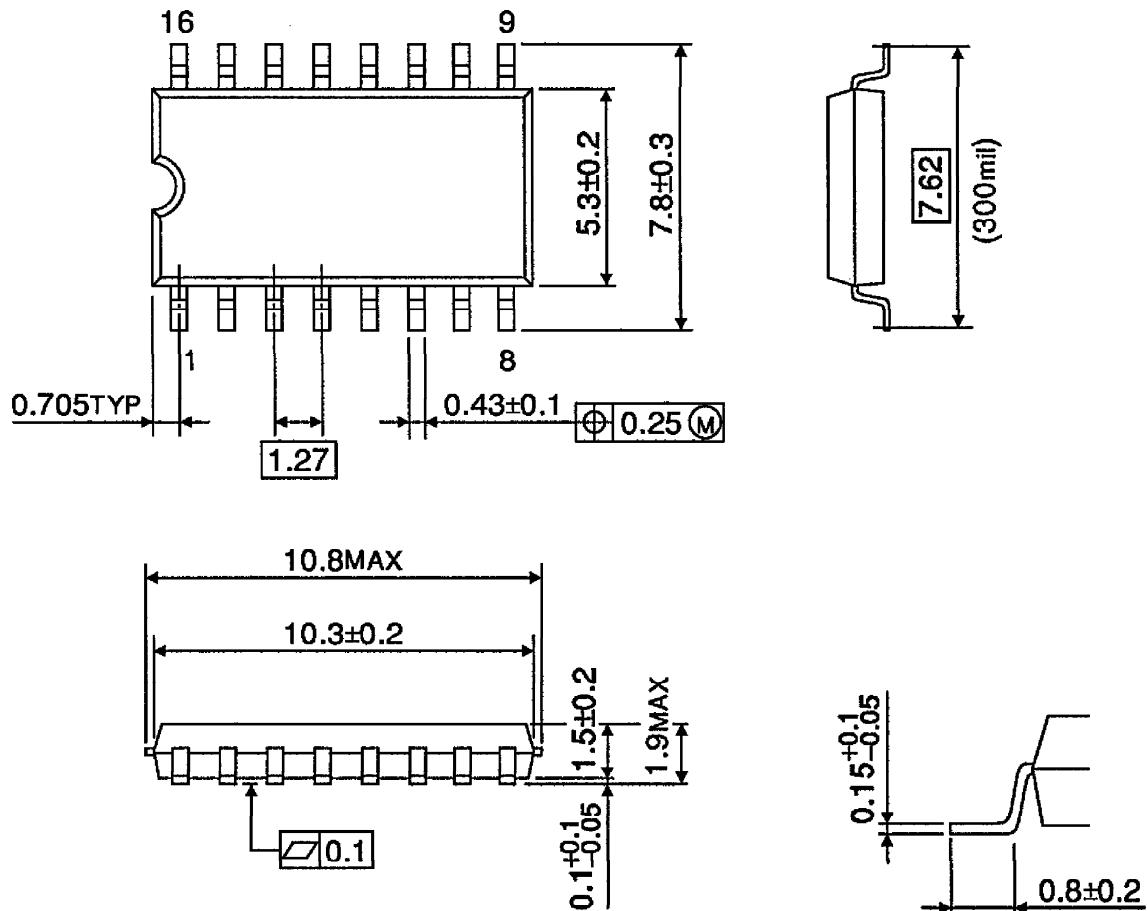
Fig.1

**AC WAVEFORM**Fig.2 t_{pLH}, t_{pHL} Fig.3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$ 

OUTLINE DRAWING

SOP16-P-300-1.27

Unit : mm



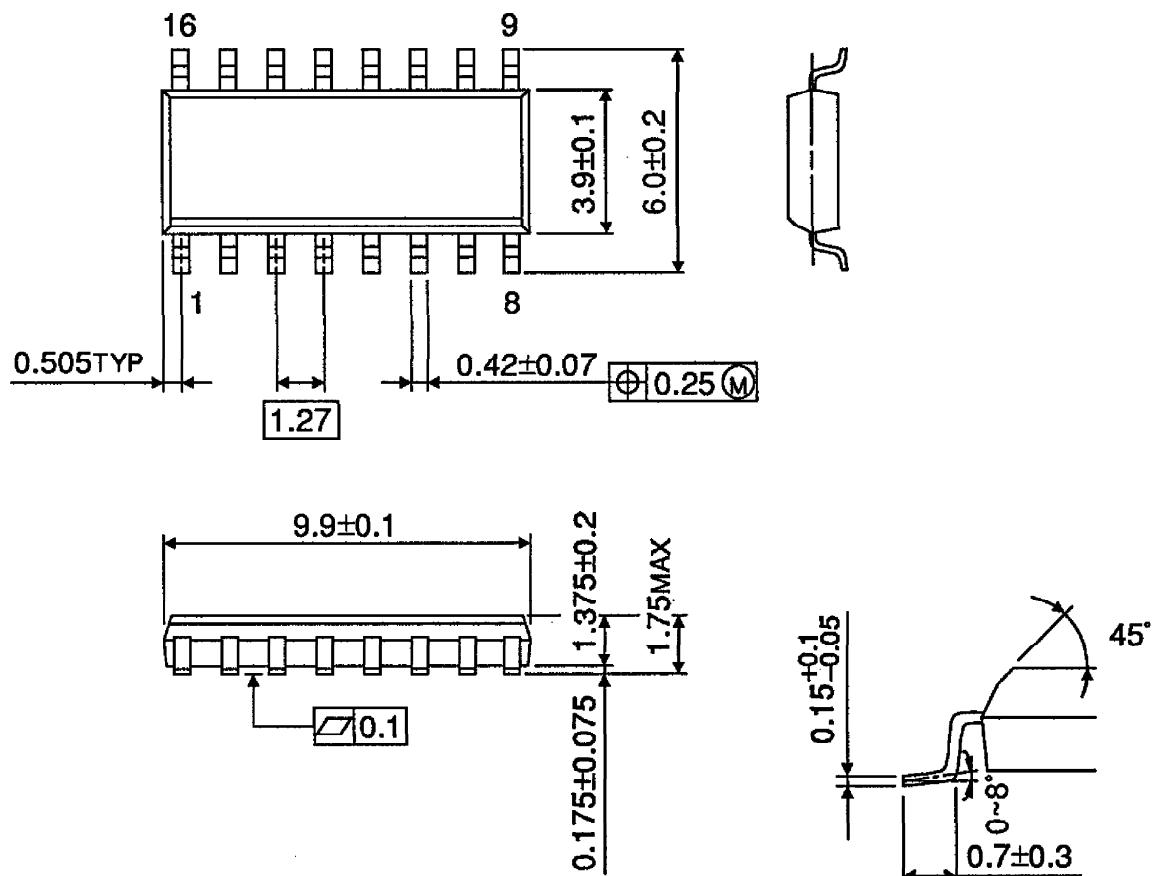
Weight : 0.18g (Typ.)

OUTLINE DRAWING

SOL16-P-150-1.27

Unit : mm

(Note) This package is not available in Japan.

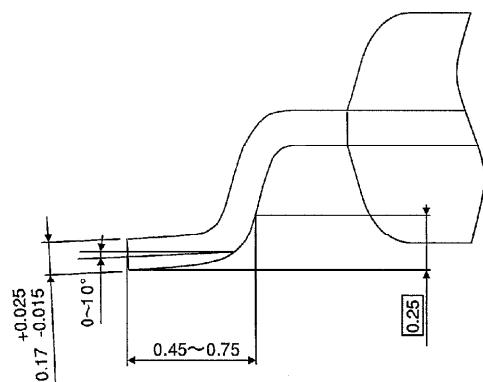
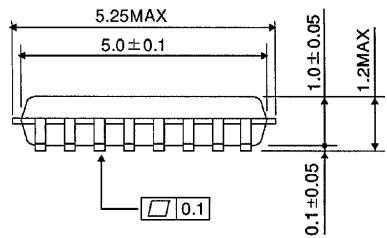
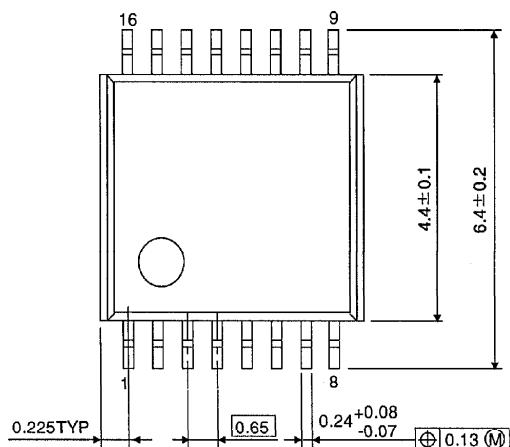


Weight : 0.12g (Typ.)

OUTLINE DRAWING

TSSOP16-P-0044-0.65

Unit : mm



Weight : 0.06g (Typ.)